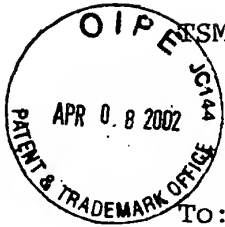


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ESMC-01-614

March 22, 2002

To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572
20 McIntosh Drive
Poughkeepsie, N.Y. 12603

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Subject:

Serial No. 10/055,059 01/23/02

Chuan-Chieh Huang et al.

METHOD TO IMPROVE VIA OR CONTACT
HOLE PROFILE USING AN IN-SITU POLYMER
DEPOSITION AND STRIP PROCEDURE

Grp. Art Unit: 2812

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INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Statement
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner of Patents and
Trademarks, Washington, D.C. 20231, on April 1, 2002.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

Signature 4/1/02

U.S. Patent 6,130,169 to Shields et al., "Efficient In-Situ Resist Strip Process for Heavy Polymer Metal Etch," discloses an in-situ resist strip process to remove polymer on the sidewalls. The 4th step uses a O₂ containing plasma.

U.S. Patent 5,925,577 to Solis, "Method for Forming Via Contact Hole in a Semiconductor Device," discloses a process to form and remove in-situ polymer from the sidewalls of via holes.

U.S. Patent 6,228,775 to Coburn et al., "Plasma Etching Method Using Low Ionization Potential Gas," discloses an etching method for forming an opening.

U.S. Patent 5,928,967 to Radens et al., "Selective Oxide-to-Nitride Etch Process Using C₄F₈/CO/AR," discloses a dry etch process for use in the fabrication of integrated circuits which use SiN etch stop layers.

U.S. Patent 6,232,237 to Tamaoka et al., "Method for Fabricating Semiconductor Device," discloses a method for fabricating a semiconductor device.

U.S. Patent 5,851,302 to Solis, "Method for Dry Etching Sidewall Polymer," discusses a method of plasma etching photoresist and sidewall polymer with an etch gas mixture.

U.S. Patent 6,130,166 to Yeh, "Alternative Plasma Chemistry for Enhanced Photoresist Removal," discusses a method where a $\text{CF}_4/\text{H}_2\text{O}_2$ plasma is used to remove residues remaining after an ashing step.

Sincerely,

A handwritten signature in black ink, appearing to read 'SBA', written over the word 'Sincerely,'.

Stephen B. Ackerman,
Reg. No. 37761

